



Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

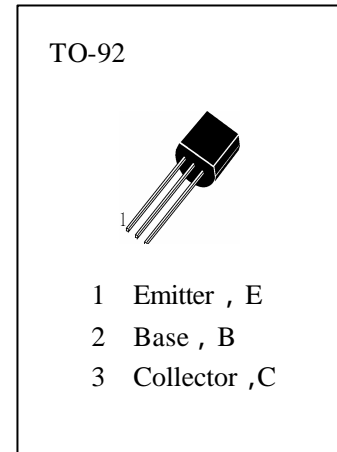
**H2907A**

**APPLICATIONS**

GENERAL PURPOSE APPLICATION.  
SWITCHING APPLICATIONS

**ABSOLUTE MAXIMUM RATINGS (  $T_a=25$  )**

- $T_{stg}$ —Storage Temperature..... -55~150
- $T_j$ —Junction Temperature.....150
- $P_C$ —Collector Dissipation.....625mW
- $V_{CBO}$ —Collector-Base Voltage.....-60V
- $V_{CEO}$ —Collector-Emitter Voltage.....-60V
- $V_{EBO}$ —Emitter-Base Voltage.....-5V
- $I_C$ —Collector Current.....-600mA



**ELECTRICAL CHARACTERISTICS (  $T_a=25$  )**

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
$BV_{CBO}$	Collector-Base Breakdown Voltage	-60			V	$I_C=-10\mu A, I_E=0$
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	-60			V	$I_C=-10mA, I_B=0$
$BV_{EBO}$	Emitter-Base Breakdown Voltage	-5			V	$I_E=-10\mu A, I_C=0$
$I_{CBO}$	Collector Cut-off Current			-10	nA	$V_{CB}=-50V, I_E=0$
$H_{FE(1)}$	DC Current Gain	75				$V_{CE}=-10V, I_C=-0.1mA$
$H_{FE(2)}$		100		300		$V_{CE}=-10V, I_C=-150mA$
$H_{FE(3)}$		50				$V_{CE}=-10V, I_C=-500mA$
$V_{CE(sat1)}$	Collector- Emitter Saturation Voltage			-0.4	V	$I_C=-150mA, I_B=-15mA$
$V_{CE(sat2)}$				-1.6	V	$I_C=-500mA, I_B=-50mA$
$V_{BE(sat1)}$	Base-Emitter Saturation Voltage			-1.3	V	$I_C=-150mA, I_B=-15mA$
$V_{BE(sat2)}$				-2.6	V	$I_C=-500mA, I_B=-50mA$
$f_T$	Current Gain-Bandwidth Product	200			MHz	$V_{CE}=-20V, I_C=-50mA, f=100MHz$
$C_{ob}$	Output Capacitance			8	pF	$V_{CB}=-10V, I_E=0, f=1MHz$
$t_{ON}$	Turn-On Time			45	nS	$V_{CC}=-30V$ $I_C=-150mA$ $I_{B1}=-15mA$
$t_D$	Delay Time			10	nS	
$t_R$	Rise Time			40	nS	
$t_{OFF}$	Turn-Off Time			100	nS	$V_{CC}=-6V$ $I_C=-150mA$ $I_{B1}=I_{B2}=-15mA$
$t_{STG}$	Storage Time			80	nS	
$t_F$	Fall Time			30	nS	

